TOSHIBA Power Module Silicon N Channel IGBT

# **MIG100J201HC**

### High Power Switching Applications Motor Control Applications

• Integrates inverter, brake power circuits & control circuits (IGBT drive units, protection units for over-current, under-voltage & over-temperature) in one package.

• The electrodes are isolated from case.

• High speed type IGBT :  $V_{CE (sat)} = 2.8 \text{ V (Max.)}$ 

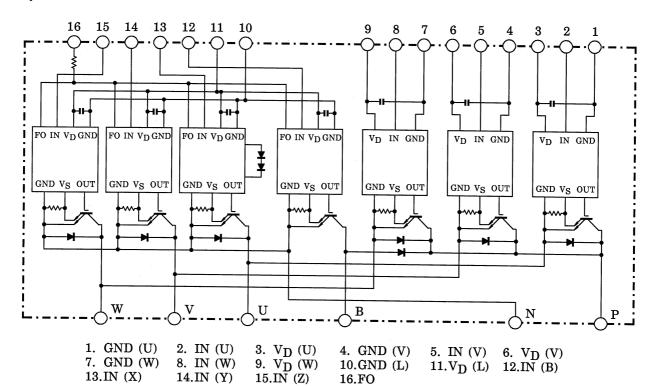
 $t_{off} = 3.0 \ \mu s \ (Max.)$ 

 $t_{rr} = 0.30 \ \mu s \ (Max.)$ 

• Outline: TOSHIBA 2-110A1A

• Weight: 520 g

#### **Equivalent Circuit**



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# Maximum Ratings ( $T_j = 25$ °C)

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P-N power terminal	V <sub>CC</sub>	450	V
	Collector-emitter voltage	_	V <sub>CES</sub>	600	V
	Collector current	T <sub>C</sub> = 25°C, DC	Ic	100	Α
inverter	Forward current	T <sub>C</sub> = 25°C, DC	l <sub>F</sub>	100	Α
	Collector power dissipation	T <sub>C</sub> = 25°C	PC	300	W
	Junction temperature	_	Tj	150	°C
Brake	Supply voltage	P-N power terminal	V <sub>CC</sub>	450	V
	Collector-emitter voltage	_	V <sub>CES</sub>	600	V
	Collector current	T <sub>C</sub> = 25°C, DC	I <sub>C</sub>	30	Α
	Reverse voltage	_	V <sub>R</sub>	600	V
	Forward current	$T_C = 25^{\circ}C$ , DC	lF	30	Α
	Collector power dissipation	T <sub>C</sub> = 25°C	PC	80	W
	Junction temperature	_	Tj	150	°C
Control	Control supply voltage	V <sub>D</sub> -GND terminal	V <sub>D</sub>	20	V
	Input voltage	IN-GND terminal	V <sub>IN</sub>	20	V
	Fault output voltage	FO-GND (L) terminal	V <sub>FO</sub>	20	V
	Fault output current	FO sink current	I <sub>FO</sub>	14	mA
	Operating temperature	_	TC	-20 ~ +100	°C
Module	Storage temperature range	_	T <sub>stg</sub>	-40 ~ +125	°C
	Isolation voltage	AC 1 minute	V <sub>ISO</sub>	2500	V
	Screw torque	M5	_	3	N·m

# Electrical Characteristics ( $T_j = 25$ °C)

### a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> = 600 V	T <sub>j</sub> = 25°C	_	_	1	mA
			T <sub>j</sub> = 125°C	_	_	20	
Collector-emitter	V <sub>CE (sat)</sub>	$V_D = 15 \text{ V}, I_C = 100 \text{ A}$ $V_{IN} = 15 \text{ V} \rightarrow 0 \text{ V}$	T <sub>j</sub> = 25°C	ı	2.3	2.8	V
saturation voltage			T <sub>j</sub> = 125°C	_	2.3	_	V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 100 A		_	2.1	3.3	V
	t <sub>on</sub>	V <sub>CC</sub> = 300 V, I <sub>C</sub> = 100 A V <sub>D</sub> = 15 V, V <sub>IN</sub> = 15 V ↔ 0 V		_	1.0	2.0	-
Switching time	t <sub>off</sub>			_	1.7	3.0	
Owntoning time	t <sub>f</sub>	Inductive load	(Note 1)	_	0.2	0.5	μs
	t <sub>rr</sub>		(Note 1)	_	0.1	0.3	



### b. Brake Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Cellector cut-off current	ICEX	V <sub>CEX</sub> = 600V	T <sub>j</sub> = 25°C	_	_	1	- mA
Cellector cur-on current			T <sub>j</sub> = 125°C	_	_	20	
Collector emitter saturation voltage	V <sub>CE</sub> (sat)	$V_D = 15V, I_C = 30A$ $V_{IN} = 15V \rightarrow 0V$	T <sub>j</sub> = 25°C	_	1.7	2.7	V
Collector-emitter saturation voltage			T <sub>j</sub> = 125°C	_	1.6	_	
Reverse current	I <sub>R</sub>	V <sub>R</sub> =600V	T <sub>j</sub> = 25°C	_	_	1	mA
Reverse current			T <sub>j</sub> = 125°C	_	_	20	
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30A		_	2.0	2.5	V
	t <sub>on</sub>	V <sub>CC</sub> = 300V, I <sub>C</sub> = 30A V <sub>D</sub> = 15V, V <sub>IN</sub> = 15V ↔ 0V		_	0.9	2.0	
Switching time	t <sub>off</sub>			_	1.7	3.0	
Switching time	t <sub>f</sub>	Inductive load	(Note 1)	_	0.25	0.5	μs
	t <sub>rr</sub>		(Note 1)	-	0.15	0.3	

## c. Control Stage $(T_j = 25^{\circ}C)$

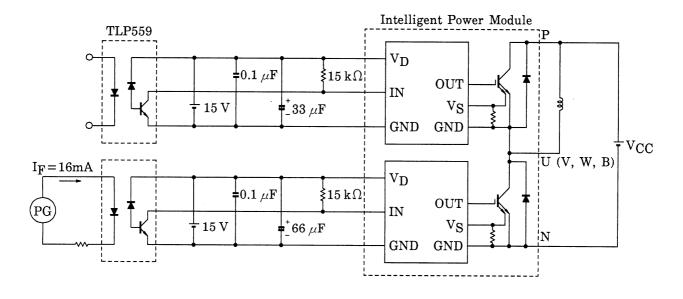
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Control circuit current	High side	I <sub>D (H)</sub>	V <sub>D</sub> = 15 V	_	8	_	mA
	Low side	I <sub>D (L)</sub>		_	35	_	IIIA
Input-on signal voltage		V <sub>IN (on)</sub>	V <sub>D</sub> = 15 V, I <sub>C</sub> = 100 mA	1.3	1.5	1.7	V
Input-off signal voltage		V <sub>IN (off)</sub>	V <sub>D</sub> = 15 V, I <sub>C</sub> = 100 mA	2.2	2.5	2.8	V
Fault output current	Protection	I <sub>FO (on)</sub>	V <sub>D</sub> = 15 V	8	10	12	mA
	Normal	I <sub>FO (off)</sub>		_	_	1	
Over current protection trip level	Inverter	OC	V = 45 V T = 425°C	160	200	_	Α
	Brake		$V_D = 15 \text{ V}, T_j = 125^{\circ}\text{C}$	40	_	_	A
Short current protection trip level	Trip level	00	V <sub>D</sub> = 15 V, T <sub>j</sub> = 125°C	240	300	_	Α
	Reset level	SC		60	_	_	A
Over current cut-off time		t <sub>off (OC)</sub>	V <sub>D</sub> = 15 V	_	5	_	μs
Over temperature protection	Trip level	ОТ	Case temperature	110	118	125	°C
	Reset level	OTr		_	80	_	
Control supply under voltage protection	Trip level	UV	11.0	12.0	12.5	V	
	Reset level	UVr	] _	_	12.5	_	V
Fault output pulse width		t <sub>FO</sub>	V <sub>D</sub> = 15 V	1	2	3	ms

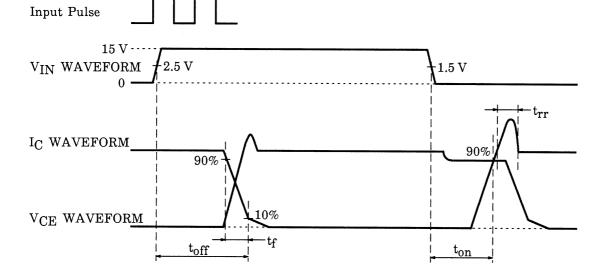


### d. Thermal Resistance ( $T_j = 25$ °C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	ance R <sub>th (j-c)</sub>	Inverter IGBT stage	_	_	0.418	·°C/W
Junction to case thermal resistance		Inverter FRD stage	_	_	1.000	
		Brake IGBTstage	_	_	1.562	
		Brake FRD stage	_	_	2.000	
Case to fin thermal resistance	R <sub>th (c-f)</sub>	Compound is applied	_	0.05	_	°C/W

Note 1: Switching time test circuit & timing chart

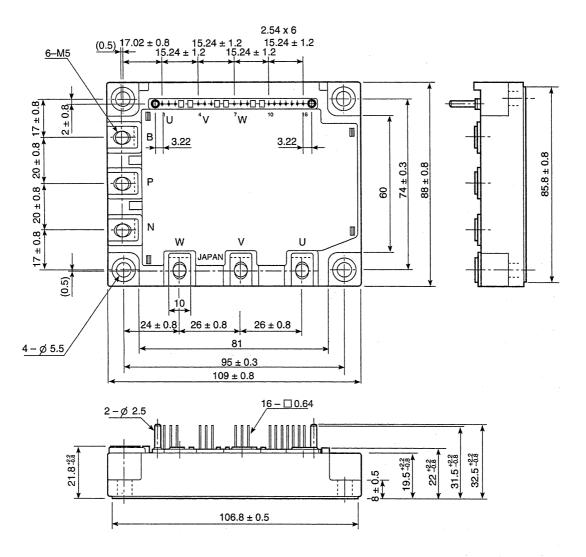




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#### Package Dimensions: TOSHIBA 2-110A1A

Unit: mm



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